

AUTOMOTIVE CURRENT TRANSDUCER OPEN LOOP TECHNOLOGY HAH3DR 800-S03/SP4





Introduction

The HAH3DR-S03 family is a tri-phase transducer for DC, AC, or pulsed currents measurement in high power and low voltage automotive applications. It offers a galvanic separation between the primary circuit (high power) and the secondary circuit (electronic circuit).

The HAH3DR-S03 family gives you a choice of having different current measuring ranges in the same housing (from ± 200 up to ± 900 A).

Features

- · Open Loop transducer using the Hall effect sensor
- Low voltage application
- Unipolar +5 V DC power supply
- Primary current measuring range up to ±800 A
- Maximum RMS primary admissible current: limited by the busbar, the magnetic core or ASIC T < +150 °C
- Operating temperature range: -40 °C < T < +125 °C
- Output voltage: fully ratiometric (in sensitivity and offset).

Special feature

Tri-phase transducer.

Advantages

- Excellent accuracy
- Very good linearity
- · Very low thermal offset drift
- · Very low thermal sensitivity drift
- High frequency bandwith
- No insertion losses
- · Very fast delay time.

Automotive applications

- Starter Generators
- Inverters
- HEV applications
- EV applications
- DC / DC converter.

Principle of HAH3DR family

The open loop transducers uses a Hall effect integrated circuit. The magnetic flux density B, contributing to the rise of the Hall voltage, is generated by the primary current IP to be measured. The current to be measured IP is supplied by a current source i.e. battery or generator (Figure 1). Within the linear region of the hysteresis cycle, B is proportional to:

$$B(I_p) = a \times I_p$$

The Hall voltage is thus expressed by:

$$U_{H} = (c_{H}/d) \times I_{H} \times a \times I_{P}$$

Except for $I_{\rm p}$, all terms of this equation are constant. Therefore:

$$\begin{array}{lll} U_{\rm H} = b \times I_{\rm p} \\ a & {\rm constant} \\ b & {\rm constant} \\ c_{\rm H} & {\rm Hall~coefficient} \\ d & {\rm thickness~of~the~Hall~plate} \\ I_{\rm H} & {\rm current~across~the~Hall~plates} \end{array}$$

The measurement signal $\,U_{\rm H}$ amplified to supply the user output voltage or current.

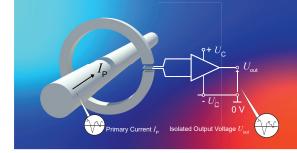


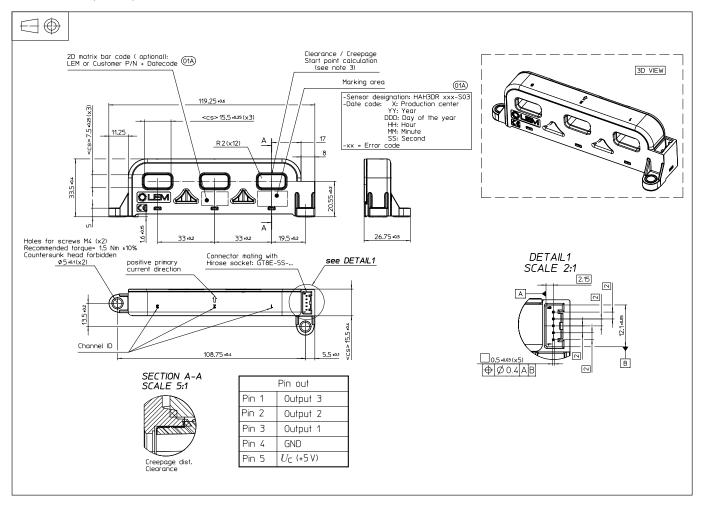
Fig. 1: Principle of the open loop transducer.

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Dimensions (in mm)

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Mechanical characteristics

• Plastic case >PBT-GF30< (natural)

Magnetic core
 FeSi wound core

Pins Copper alloy gold plated

• Mass 97 g ±5 %

• IP level IPxx

Mounting recommendation

• Mating connector type Hirose Socket GT8E-5S-...

Assembly torque max 1.5 N.m ±10 %

 The clamping force must be applied to the compression limiter, washer recommended.

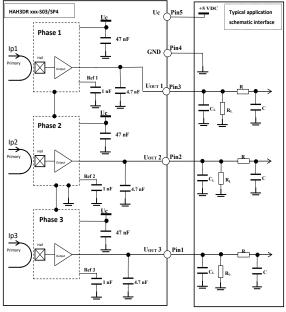
 $R_{\rm L}$ > 10 k $\!\Omega$ optional resistor for signal line diagnostic

 $\overline{C_L}$ < 2.2 nF EMC protection RC: low pass filter (optional)

Remark

• $U_{\rm out}$ > $U_{\rm O}$ when $I_{\rm P}$ flows in the positive direction (see arrow on drawing).

System architecture (example)



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Absolute ratings (not operating)

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Parameter	Cumbal	Unit	Specification			Conditions	
Parameter	Syllibol		Min	Typical	Max	Conditions	
			-0.5		8	Continuous not operating	
Maximum supply voltage	$U_{\rm C\; max}$	V			6.5	Exceeding this voltage may temporarily reconfigure the circuit until the next power on	
Output voltage low 1)	$U_{\rm outL}$	V			0.2	@ $U_{\rm C}$ = 5 V, $T_{\rm A}$ = 25 °C	
Output voltage high 1)	U_{outH}	V	4.8				
Ambient storage temperature	T_{Ast}	°C	-50		125		
Electrostatic discharge voltage (HBM)	U_{ESDHBM}	kV			2	JESD22-A114-B class 2	
RMS voltage for AC insulation test	U_{d}	kV			2.5	50 Hz, 1 min, IEC 60664 part1	
Creepage distance	d_{Cp}	mm	F 00				
Clearance	d_{CI}	mm		5.08			
Comparative tracking index	CTI			PLC3			
Insulation resistance	R_{INS}	ΜΩ	500			500 V DC, ISO 16750	
Primary nominal peak current	\hat{I}_{PN}	Α			2)		

Operating characteristics in nominal range (I_{PN})

	Symbol	Unit	Specification			
Parameter			Min	Typical	Max	Conditions
		Elect	rical Da	ıta		
Primary current, measuring range	I_{PM}	Α	-800		800	
Primary nominal RMS current	I_{PN}	Α	-800		800	
Supply voltage 1)	U_{C}	V	4.75	5	5.25	
Ambient operating temperature	T_{A}	°C	-40		125	
Load capacitance	C_{L}	nF			2.2	
Output voltage (Analog) 1)	U_{out}	V	$U_{\text{out}} = (U_{\text{C}}/5) \times (U_{\text{o}} + S \times I_{\text{P}})$		$_{\rm o}$ + $S \times I_{\rm p}$)	@ U _c
Sensitivity 1)	S	mV/A		2.5		@ U _c = 5 V
Offset voltage	U_{o}	V		2.5		
Current consumption (for 3 phases)	I_{C}	mA		45	60	@ $U_{\rm C}$ = 5 V, @ -40 ° C < $T_{\rm A}$ < 125 °C
Load resistance	R_{L}	ΚΩ	10			
Output internal resistance	$R_{\rm out}$	Ω			10	DC to1 kHz
Perfo	rmance Da	ita @ 3 S	igma (ind	luding phas	ses coupling))
Ratiometricity error	$\varepsilon_{\rm r}$	%		0.5		
Compitivity orner	$\varepsilon_{_S}$	%		±0.5		@ T _A = 25 °C
Sensitivity error				±1		@ T _A = 25 °C, After T ° Cycles
Electrical offset voltage	U_{OE}	mV		±4		@ $T_{\rm A}$ = 25 °C, @ $U_{\rm C}$ = 5 V
Magnetic offset voltage @ I_p = 0 V	U_{OM}	mV	-7.5		7.5	@ $T_{\rm A}$ = 25 °C, @ $U_{\rm C}$ = 5 V
Average temperature coefficient of U_{OE}	$TCU_{ extsf{OEAV}}$	mV/°C	-0.08		0.08	@ -40 ° C < T _A < 125 °C
Average temperature coefficient of S	TCS_{AV}	%/°C	-0.03	±0.01	0.03	@ $-40 ^{\circ}$ C < T_{A} < 125 $^{\circ}$ C
Linearity error	ε_{L}	% I _P	-1		1	@ $U_{\rm C}$ = 5 V, @ $T_{\rm A}$ = 25 °C, @ I = $I_{\rm PM}$
Delay time to 90 % of the final output value for $I_{\rm PN}$ step	t _{D 90}	μs		4	6	$di/dt = 100 \text{ A/}\mu\text{s}$
Frequency bandwidth 2)	BW	kHz	40			@ -3 dB
Peak-to-peak noise voltage	$U_{ m no\;pp}$	mV			10	@ DC to 1 MHz
Phase shift	$\Delta \varphi$	0	-4		0	@ DC to 1 KHz

 $\underline{\text{Notes}}: \qquad ^{1)} \quad \text{The output voltage } \ U_{\text{out}} \ \text{is fully ratiometric. The offset and sensitivity are dependent on the supply voltage } \ U_{\text{C}} \ \text{relative to the following formula:}$

$$I_{\rm P} = \left(\frac{5}{U_{\rm C}} \times U_{\rm out} - U_{\rm O}\right) \times \frac{1}{S} \text{ with } S \text{ in (V/A)}$$

- ²⁾ Primary current frequencies must be limited in order to avoid excessive heating of the busbar, magnetic core and the ASIC (see feature paragraph in page 1).
- ³⁾ Transducer is not protected against reverse polarity.

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Total error



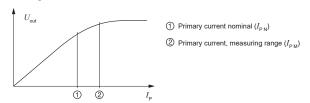
$I_{\mathbf{p}}$ (A)	Total	error @ 25 °C	(mV)	Total error @ T range (mV)		
in A	in mV	in A	in %	in mV	in A	in %
-800	±40.0	±16.0	±2.0	±70.0	±28.0	±3.50
0	±20.0	±8.0	±1.0	±30.0	±12.0	±1.50
800	±40.0	±16.0	±2.0	±70.0	±28.0	±3.50



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PERFORMANCES PARAMETERS DEFINITIONS

Primary current definition:



Definition of typical, minimum and maximum values:

Minimum and maximum values for specified limiting and safety conditions have to be understood as such as values shown in "typical" graphs. On the other hand, measured values are part of a statistical distribution that can be specified by an interval with upper and lower limits and a probability for measured values to lie within this interval. Unless otherwise stated (e.g. "100 % tested"), the LEM definition for such intervals designated with "min" and "max" is that the probability for values of samples to lie in this interval is 99.73 %. For a normal (Gaussian) distribution, this corresponds to an interval between -3 sigma and +3 sigma. If "typical" values are not obviously mean or average values, those values are defined to delimit intervals with a probability of 68.27 %, corresponding to an interval between -sigma and +sigma for a normal distribution. Typical, minimum and maximum values are determined during the initial characterization of a product.

Output noise voltage:

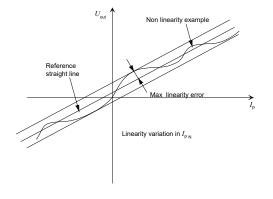
The output voltage noise is the result of the noise floor of the Hall elements and the linear amplifier.

Magnetic offset:

The magnetic offset is the consequence of an any current on the primary side. It's defined after a stated excursion of primary current.

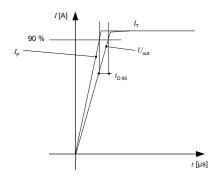
Linearity:

The maximum positive or negative discrepancy with a reference straight line $U_{\rm out}$ = $f(I_{\rm P})$. Unit: linearity (%) expressed with full scale of $I_{\rm P\,N}$.



Delay time $t_{p,qq}$:

The time between the primary current signal (I_{PN}) and the output signal reach at 90 % of its final value.



Sensitivity:

The transducer's sensitivity S is the slope of the straight line $U_{\text{out}} = f(I_{\text{P}})$, it must establish the relation:

$$U_{\text{out}}(I_{\text{P}}) = U_{\text{C}}/5 (S \times I_{\text{P}} + U_{\text{O}})$$

Offset with temperature:

The error of the offset in the operating temperature is the variation of the offset in the temperature considered with the initial offset at 25 °C.

The offset variation $I_{\text{O }T}$ is a maximum variation the offset in the temperature range:

$$I_{OT} = I_{OE} \max - I_{OE} \min$$

The offset drift TCI_{OEAV} is the I_{OT} value divided by the temperature range.

Sensitivity with temperature:

The error of the sensitivity in the operating temperature is the relative variation of sensitivity with the temperature considered with the initial offset at 25 °C.

The sensitivity variation S_{τ} is the maximum variation (in ppm or %) of the sensitivity in the temperature range: S_r = (Sensitivity max - Sensitivity min) / Sensitivity at 25 °C. The sensitivity drift $TCS_{\Delta V}$ is the S_T value divided by the temperature range. Deeper and detailed info available is our LEM technical sales offices (www.lem.com).

Offset voltage @ $I_p = 0$ A:

The offset voltage is the output voltage when the primary current is zero. The ideal value of $U_{\rm O}$ is $U_{\rm C}/2$. So, the difference of U_0 – $U_c/2$ is called the total offset voltage error. This offset error can be attributed to the electrical offset (due to the resolution of the ASIC quiescent voltage trimming), the magnetic offset, the thermal drift and the thermal hysteresis. Deeper and detailed info available is our LEM technical sales offices (www.lem. com).

Environmental test specifications:

Refer to LEM GROUP test plan laboratory CO.11.11.515.0 with "Tracking Test Plan Auto" sheet.

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Environmental test specifications:

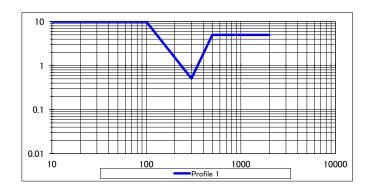
Name Standard		Conditions		
	Electrical tests			
Phase delay check	LEM Procedure	100 Hz to 100 kHz @ 50 A peak		
Noise measurement	LEM Procedure	Sweep from DC to 1 MHz		
Delay time di/dt	LEM Procedure	100 A/μs, <i>I</i> pulse = 800 A		
dv/dt	LEM Procedure	> 5 kV/µs, <i>U</i> = 1000 V		
Dielectric Withstand Voltage test	ISO 16750-2 §4.11 §4.12	2500 V AC/1 min/50 Hz		
Insulation resistance	ISO 16750-2 (2010)	500 V DC, time = 60 s $R_{\rm INS} \ge$ 500 MΩ minimum		
	Environmental test	rs		
High <i>T</i> °C, High Humidity, Electrical connection	IEC 60068-2-78 (2001)	1000 hours +85 °C/85 % RH $U_{\rm C}$ = 5 V DC, $I_{\rm P}$ = 0		
Thermal Shock	ISO 16750-4 §5.3.2 (04.2010)	1000 cycles (1000 hours), 30 min, -40 °C//30 min +125 °C $U_{\rm C}$ not connected, $I_{\rm P}$ = 0		
High T °C Storage + High T °C Exposure	ISO 16750-4 §5.1.2.1 (04.2010)	Storage: 125 °C for 1000 hours $U_{\rm C}$ not connected, $I_{\rm P}$ = 0 for both tests		
Mechanical Shock	ISO 16750-3 §4.2.2 (12.2012)	50 g/6 ms Half Sine @ 25 °C 10 shocks of each direction (Total: 60) $U_{\rm C}$ not connected, $I_{\rm P}$ = 0		
Random Vibration in <i>T</i> °C	om Vibration in <i>T</i> °C ISO 16750-3 §4.1.2.4 (12.2012)			
1	EMC tests			
Radiated Emission Absorber Lined Shielded Enclosure (ALSE)	CICOD 16			
Radiated Immunity Bulk Current Injection (BCI)	GMW3097 (2006) §3.4.1 ISO 11452-1 & - 4	1 MHz to 400 MHz Level: Level 2 (table 11)		
Radiated Immunity Anechoic chamber	GMW3097 (2006) §3.4.2 ISO 11452-1 & - 2	400 MHz to 2000 MHz Level: Level 2 (table 12)		
ESD Test	GMW3097 (2006) §3.6.3	150 pF / 2000 Ω Contact: ±4, ±6 kV Air: ±8 kV $U_{\rm C}$ not connected		



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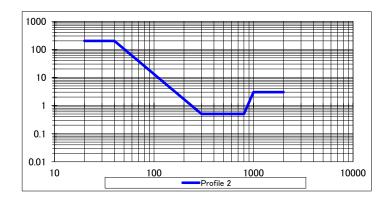
Random Vibration Profile 1 $-40 \, ^{\circ}\text{C} < T < 125 \, ^{\circ}\text{C}$

Hz	PSD [(m/s²)² /Hz]
Frequency	Profile 1
10	10
100	10
300	0.51
500	5
1000	5
2000	5



Random Vibration Profile 2 $-40 \, ^{\circ}\text{C} < T < 125 \, ^{\circ}\text{C}$

Hz	PSD [(m/s²)² /Hz]
Frequency	Profile 2
20	200
40	200
300	0.5
800	0.5
1000	3
2000	3



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